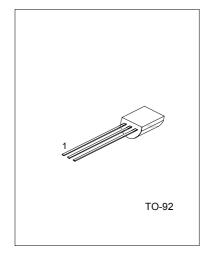
UTC 2SC1815 NPN EPITAXIAL SILICON TRANSISTOR

AUDIO FREQUENCY AMPLIFIER HIGH FREQUENCY OSC NPN **TRANSISTOR**

FEATURES

- *Collector-Emitter voltage:
- BVcEo=50V
- *Collector current up to 150mA
- * High hFE linearity
- *complimentary to 2SA1015



1:EMITTER 2:COLLECTOR 3. BASE

ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

(
PARAMETER	SYMBOL	RATING	UNIT			
Collector-base voltage	Vсво	60	V			
Collector-emitter voltage	VCEO	50	V			
Emitter-base voltage	VEBO	5	V			
Collector dissipation(Ta=25°C)	Pc	400	mW			
Collector current	lc	150	mA			
Base current	lв	50	mA			
Junction Temperature	Tj	125	°C			
Storage Temperature	Tstg	-55 ~ +150	°C			

ELECTRICAL CHARACTERISTICS(Ta=25°C,unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector cut-off current	Ісво	Vcb=60V,IE=0			100	nA
Emitter cut-off current	IEBO	V _{EB} =5V,Ic=0			100	nA
DC current gain(note)	hFE1	Vce=6V,lc=2mA	70		700	
	hFE2	VcE=6V,Ic=150mA	25			
Collector-emitter saturation voltage	Vce(sat)	Ic=100mA,IB=10mA		0.1	0.25	V
Base-emitter saturation voltage	V _{BE} (sat)	Ic=100mA,I _B =10mA			1.0	V
Current gain bandwidth product	fτ	VcE=10V,Ic=50mA	80			MHz
Output capacitance	Cob	V _{CB} =10V,I _E =0,f=1MHz		2.0	3.0	pF
Noise Figure	NF	Ic=-0.1mA,VcE=6V		1.0	1.0	dB
_		R _G =10kΩ,f=100Hz				

UTC UNISONIC TECHNOLOGIES CO. LTD

UTC 2SC1815 NPN EPITAXIAL SILICON TRANSISTOR

CLASSIFICATION OF hFE1

RANK	Υ	G	L
RANGE	120-240	200-400	350-700

TYPICAL CHARACTERISTIC CURVES

